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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/634,964	08/05/2003	Zhendong Liu	02039US	6941
61611	7590	08/18/2006	EXAMINER	
ROHM AND HAAS ELECTRONIC MATERIALS CMP HOLDINGS, INC. 451 BELLEVUE ROAD NEWARK, DE 19713				GEORGE, PATRICIA ANN
ART UNIT		PAPER NUMBER		
		1765		

DATE MAILED: 08/18/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/634,964	LIU, ZHENDONG
	Examiner	Art Unit
	Patricia A. George	1765

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 20 June 2006.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

,8-9

- 4) Claim(s) 1,2 and 4-6 is/are pending in the application.
- 4a) Of the above claim(s) 8-9 is/are withdrawn from consideration.
- 5) Claim(s) _____ is/are allowed.
- 6) Claim(s) 1,2, 4, 5, 6 is/are rejected.
- 7) Claim(s) _____ is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. _____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____
3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.	5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)
	6) <input type="checkbox"/> Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1, 2, 4, 5, and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sun et al (US Patent No. 6,709,316) in view of Sherber et al. (5,858,813), evidenced by Changzhou Kejia Chemical Co. (Product Detail Poly (Maleic Acid)) and Wikipedia; Maleic Acid

(http://www.echinachem.com/kejiachem.co/Product_Detail.aspx?Gold_Product_Profile_ID=404).

The reference of Sun et al discloses an aqueous chemical mechanical planarizing composition (col. 9, l. 14). The composition comprises an oxidizer in the form of promoting barrier removal since the composition is the same (col. 6, lines 57-59); an abrasive in the form of (col. 7, lines 9-12); an inhibitor in the form of (for decreasing removal of a metal interconnect) (col. 6, lines 59-65). In addition, Sun et al. clearly discloses ph-adjusting agent/s can adjust the CMP composition to a range of about 2.5 to about 11, which encompassed the claimed less than 4. Sun et al. also clearly explain the adjusting agents can be comprised of bases, inorganic acids, and/or

organic acids (col.6, l.66 to col.7, l.3). Sun teaches a tantalum nitride removal rate of at least eighty percent of copper removal rate (col.3, lines32-34). Sun cites a 1:0:0 removal rate which indicates that 100% of the barrier layer (i.e. TaN) is removed relative to 0% of the copper and 0% of the dielectric.

In addition Sun teaches a pad pressure of 13.8 kPa. (col. 12, line 1) which is within Sun's range of 1 to 8 psi (6.895 kPa to 55.158 kPa). Sun broadly discloses the use of a chelating agent (col.6, lines 49-54), including the use of carboxyl acids (see claim 10).

Sun fails to disclose the use of water-soluble polymers comprises polymaleic acid (as in claim 1); or polymaleic acid comprises a homo or copolymer (as in claim 2).

Sherber teaches a composition for metal layers and other films during the various stages of multilevel interconnect (i.e. barrier films such as TaN) comprises the conventional use of derivatives from maleic acid, i.e. a water-soluble homopolymer polymaleic acid [evidenced by Wikipedia; Maleic Acid (for solubility) and Changzhou Kejia Chemical Co . (maleic acid is homopolymer)], because they posses the ability to complex or associate with dissolving metals and improve the removal rate of metal thin films such as titanium, and the like, during the CMP process (see col. 5, lines 43-58).

It would have been obvious to one of ordinary skill in the art at the time of invention was made, to include a water soluble polymaleic acid, as Sherber, when forming the CMP composition of Sun, because Sherber teaches use of derivatives of the water soluble organic acid, maleic acid, posses the ability to complex with the

dissolving metals to improve the removal rate of the metal films, a well known process improvement.

As to claim 4, see Sun's teaching on pH above, also see Sherber's teaching that pH can be increased or decreased for a desired range (col.4, lines 41-42).

It would have been obvious to one of ordinary skill in the art at the time the invention was made, to select any desired range of pH, between 2.5 and 11, as Sun, to provide desired results, as Sherber, because overlapping ranges have been held to be obvious.

As to claim 5, Sun teaches an aqueous chemical mechanical planarizing composition comprising 0.05 to 15 wt % abrasive (col. 7, lines 9-12); 0.1 to 10 wt % oxidizing agent (col. 6, lines 57-59); and 0.02 to 1 wt% benzotriazole (col. 6, lines 59-65) which falls within the range of the instant invention. In addition, Sun et al. clearly discloses ph-adjusting agent/s can adjust the CMP composition to a range of about 2.5 to about 11, which encompassed the claimed less than 4. Sun et al. also clearly explain the adjusting agents can be comprised of bases, inorganic acids, and/or organic acids (col.6, l.66 to col.7, l.3). Furthermore, Sun et al. teaches use of phosphoric and nitric acids as a pH-adjusting agents (col.7, l. 3-4 and l.59). Sun et al. teaches a tantalum nitride removal rate of at least eighty percent of copper removal rate (col.3, lines32-34). Sun cites a 1:0:0 removal rate which indicates that 100% of the barrier layer (i.e. TaN) is removed relative to 0% of the copper and 0% of the dielectric

at a pad pressure of 13.8 kPa. (col. 12, line 1) with in Sun's range of 1 to 8 psi (6.895 kPa to 55.158 kPa). Sun's range is within the claimed range.

Sun fails to disclose the use of water-soluble polymers.

Sherber teaches a composition for metal layers and other films during the various stages of multilevel interconnect (i.e. barrier films such as TaN) comprises the conventional use of derivatives from maleic acid, i.e. a water-soluble homopolymer polymaleic acid [evidenced by Wikipedia; Maleic Acid (for solubility) and Changzhou Kejia Chemical Co . (maleic acid is homopolymer)], because they posses the ability to complex or associate with dissolving metals and improve the removal rate of metal thin films such as titanium, and the like, during the CMP process (see col. 5, lines 43-58).

It would have been obvious to one of ordinary skill in the art at the time of invention was made, to include a water soluble polymaleic acid, as Sherber, when forming the CMP composition of Sun, because Sherber teaches use of derivatives of the water soluble organic acid, maleic acid, posses the ability to complex with the dissolving metals to improve the removal rate of the metal films, a well known process improvement.

As to claims 6, see the discussion above toward claim 2.

Response to Remarks

As to applicants' remarks, in regard to the Declaration of applicant Dr. Liu, please see Response to Declaration, starting on page 5, of the action filed 3/21/2006.

Applicant's arguments, on page 6, paragraph 1, filed 6/20/2006, with respect to the reference of Yano has been fully considered and is persuasive. The rejection of 3/21/2006 has been withdrawn.

Applicants' continue to argue, on page 5 as in remarks of 10/21/2005, that the reference of Sun et al. does not disclose a second step which operates at a pH below 4, adjusted with an inorganic acid for use in a barrier slurry. Sun et al. clearly discloses ph adjusting agent/s can adjust the CMP composition to a range of about 2.5 to about 11, which encompassed the claimed less than 4. Sun et al. also clearly explain the adjusting agents can be comprised of bases, inorganic acids, and/or organic acids (col.6, 1.66 to col.7, 1.3). That the reference of Sun et al. does not disclose a selective second step is noted but not persuasive because the tantalum removal rate of the solution is properly ascribed to the solution and not an active process step.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Colloidal Dynamics; The CMP Slurry Monitor - Background.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Patricia A. George whose telephone number is (571) 272-5955. The examiner can normally be reached on weekdays from 7:00am to

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4:30pm. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

PAG
08/06

NADINE NORTON
SUPERVISORY PATENT EXAMINER
ART UNIT 1765

